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AUG 17 2006

Amendments to the Claims

1. (Original) A process of making a magnetoresistive memory device comprising:  
  
making a mask having stepped bit ends;  
  
using the mask to make a magnetic storage layer having tapered bit ends;  
  
using the mask to make a magnetic sense layer having tapered bit ends; and,  
  
using the mask to make a non-magnetic layer between the magnetic sense layer and the magnetic storage layer, and wherein the non-magnetic layer has tapered bit ends.
2. (Currently Amended) The process of claim 1 wherein the magnetic storage layer comprises more than one or more magnetic storage ~~[[films]]~~ film.
3. (Original) The process of claim 1 wherein the magnetic storage layer comprises first and second magnetic storage films, wherein the first magnetic storage film comprises NiFe, and wherein the second magnetic storage film comprises CoFe.
4. (Currently Amended) The process of claim 1 wherein the magnetic sense layer comprises more than one or more magnetic sense ~~[[films]]~~ film.
5. (Original) The process of claim 1 wherein the magnetic sense layer comprises first and second magnetic sense films, wherein the first magnetic sense film comprises NiFe, and wherein the second magnetic sense film comprises CoFe.

6. (Currently Amended) The process of claim 1 wherein the magnetic storage layer comprises more than one or more magnetic storage ~~[[films]]~~ film, and wherein the magnetic sense layer comprises more than one or more magnetic sense ~~[[films]]~~ film.

7. (Original) The process of claim 1 wherein the magnetic storage layer comprises first and second magnetic storage films, wherein the magnetic sense layer comprises first and second magnetic sense films, wherein the first magnetic storage film comprises NiFe, wherein the second magnetic storage film comprises CoFe, wherein the first magnetic sense film comprises NiFe, and wherein the second magnetic sense film comprises CoFe.

8. (Original) The process of claim 1 wherein the magnetic sense film comprises a ferromagnetic sense film.

9. (Original) The process of claim 1 wherein the magnetic storage film comprises a ferromagnetic storage film.

10. (Original) The process of claim 9 wherein the magnetic sense film comprises a ferromagnetic sense film.

11. (Original) The process of claim 1 wherein the using of the mask to make a magnetic storage layer having tapered bit ends, the using of the mask to make a magnetic sense layer having tapered bit ends, and the using of the mask to make a non-magnetic layer between the

magnetic sense layer and the magnetic storage layer are performed in a single lithographic patterning step.

12. (Original) The process of claim 1 wherein the using of the mask to make a magnetic storage layer having tapered bit ends, the using of the mask to make a magnetic sense layer having tapered bit ends, and the using of the mask to make a non-magnetic layer between the magnetic sense layer and the magnetic storage layer are performed as separate lithographic patterning steps.

13. (Cancelled)

14. (Original) A process of making a magnetoresistive memory device comprising:  
laying out a mask layout in grids having a central grid forming a central section and outer grids forming bit end sections, and wherein the grids of the bit end sections are rectangles;  
making a mask by use of the mask layout, wherein the mask has stepped bit ends;  
using the mask to make a magnetic storage layer having tapered bit ends;  
using the mask to make a magnetic sense layer having tapered bit ends; and,  
using the mask to make a non-magnetic layer between the magnetic sense layer and the magnetic storage layer, wherein the non-magnetic layer has tapered bit ends.

15. (Currently Amended) The process of claim 14 wherein the magnetic storage layer comprises more than one ~~or more~~ magnetic storage ~~[[films]]~~ film.

16. (Original) The process of claim 14 wherein the magnetic storage layer comprises first and second magnetic storage films, wherein the first magnetic storage film comprises NiFe, and wherein the second magnetic storage film comprises CoFe.

17. (Currently Amended) The process of claim 14 wherein the magnetic sense layer comprises more than one ~~or more~~ magnetic sense ~~[[films]]~~ film.

18. (Original) The process of claim 14 wherein the magnetic sense layer comprises first and second magnetic sense films, wherein the first magnetic sense film comprises NiFe, and wherein the second magnetic sense film comprises CoFe.

19. (Currently Amended) The process of claim 14 wherein the magnetic storage layer comprises more than one ~~or more~~ magnetic storage ~~[[films]]~~ film, and wherein the magnetic sense layer comprises more than one ~~or more~~ magnetic sense ~~[[films]]~~ film.

20. (Original) The process of claim 14 wherein the magnetic storage layer comprises first and second magnetic storage films, wherein the magnetic sense layer comprises first and second magnetic sense films, wherein the first magnetic storage film comprises NiFe, wherein the second magnetic storage film comprises CoFe, wherein the first magnetic sense film comprises NiFe, and wherein the second magnetic sense film comprises CoFe.

21. (Original) The process of claim 14 wherein the magnetic sense film comprises a ferromagnetic sense film.

22. (Original) The process of claim 14 wherein the magnetic storage film comprises a ferromagnetic storage film.

23. (Original) The process of claim 22 wherein the magnetic sense film comprises a ferromagnetic sense film.

24. (Original) The process of claim 14 wherein the using of the mask to make a magnetic storage layer having tapered bit ends, the using of the mask to make a magnetic sense layer having tapered bit ends, and the using of the mask to make a non-magnetic layer between the magnetic sense layer and the magnetic storage layer are performed in a single lithographic patterning step.

25. (Original) The process of claim 14 wherein the using of the mask to make a magnetic storage layer having tapered bit ends, the using of the mask to make a magnetic sense layer having tapered bit ends, and the using of the mask to make a non-magnetic layer between the magnetic sense layer and the magnetic storage layer are performed as separate lithographic patterning steps.

26. (Cancelled)